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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In ra PATENT application of:

Applicant:

Summerfelt, et al.

Application No.:

10/620,196

For:

FERROELECTRIC MEMORY CELL WITH ANGLED CELL

TRANSISTOR ACTIVE REGION AND METHODS FOR

**FABRICATING THE SAME** 

Filing Date:

July 15, 2003

Examiner:

Tran, Thien F.

Art Unit:

2811

## **REPLY TO OFFICE ACTION DATED SEPTEMBER 1, 2004**

Mail Stop Amendment Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Favorable reconsideration of the above-identified application is respectfully requested in view of the following amendment and remarks.